

AMENDMENT

Please amend the subject application as follows:

IN THE CLAIMS:

Please amend the claims as follows (complete listing of claims with markups according to Revised Format):

1-11 (canceled).

12. (currently amended) A light emitting diode structure, comprising:
a semiconductor structure for emitting light;
a metal bonding layer on the semiconductor structure;
~~a transparent substrate formed on said semiconductor structure via a said metal bonding layer and bonded with between said semiconductor structure and said transparent substrate under a bonding temperature ranged from 300 °C to 900 °C;~~ and
a first electrode and a second electrode respectively formed on said semiconductor structure and said transparent substrate for providing a current to said semiconductor structure.

13. (original) The light emitting diode structure as claimed in claim 12, wherein said semiconductor structure is a light emitting diode structure.

14. (original) The light emitting diode structure as claimed in claim 13, wherein said light emitting diode structure is formed by a four-element material of AlGaInP.

15. (original) The light emitting diode structure as claimed in claim 12, wherein said transparent substrate is one selected from a group consisting of GaP, a SiC, an AlAs, an AlGaAs and a diamond substrates.

16. (original) The light emitting diode structure as claimed in claim 12, wherein said transparent substrate is preferably a GaP substrate.

17. (original) The light emitting diode structure as claimed in claim 12, wherein said metal bonding layer is one selected from a group consisting of an AuBe, an AuSn, an AuGe, an AuNi, and an AuZn thin films.

18. (canceled).

19. (currently amended) The light emitting diode structure as claimed in claim 12, wherein said metal bonding technology is performed at transparent substrate is bonded with said semiconductor structure via said metal bonding layer under a bonding pressure ranged from 500 pounds to 5000 pounds.

20. (original) The light emitting diode structure as claimed in claim 12, wherein said first electrode and said second electrode are respectively a P-type electrode and an N-type electrode.

21. (original) The light emitting diode structure as claimed in claim 12, wherein said first electrode and said second electrode are respectively an N-type electrode and a P-type electrode.